

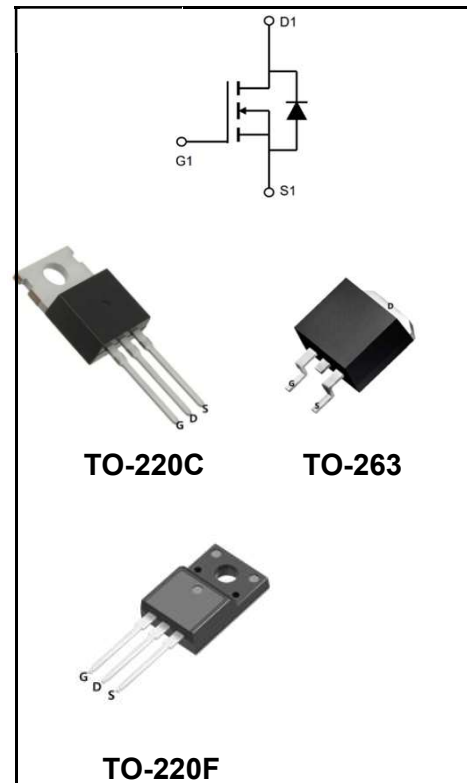
600V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	10A
V_{DSS}	600V
$R_{DS(on)-typ}(@V_{GS}=10V)$	$<0.9\Omega$ (Type: 0.75Ω)

Features

- ♦Fast Switching
- ♦Low ON Resistance
- ♦Low Gate Charge
- ♦100% Single Pulse avalanche energy Test
- ♦LeadfreeincomplywithEURoHS2011/65/EUdirectives



Mechanical Data

- ♦Case: Molded plastic
- ♦Mounting Position: Any
- ♦Molded Plastic: UL Flammability Classification Rating 94V-0
- ♦Solder bath temperature 275°C maximum, 10s per JESD22-106
- ♦Case: TO-220C, TO-220F, TO-263

Product Specification Classification

Part Number	Package	Marking	Pack
YFW10N60AC	TO-220C	YFW 10N60AC XXXXX	50PCS/Tube
YFW10N60AF	TO-220F(0.5mm)	YFW 10N60AF XXXXX	50PCS/Tube
YFW10N60AF	TO-220F(1.3mm)	YFW 10N60AF XXXXX	50PCS/Tube
YFW10N60AS	TO-263	YFW 10N60AS XXXXX	50PCS/Tube
YFW10N60AS-R	TO-263	YFW 10N60AS XXXXX	800PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value			Units
		220C	220F	263	
Drain-Source Voltage	V _{DS}	600			V
Gate-Source Voltage	V _{GS}	± 30			V
Continue Drain Current-Continuous (TC = 25°C)	I _D	10			A
-Continuous (TC = 100°C)		6			
Pulsed Drain Current (Note1)	I _{DM}	40			A
Power Dissipation	P _D	143	50	143	W
-Derate above 25°C		1.14	0.38	1.14	W/°C
Single Pulse Avalanche Energy (Note2)	E _{AS}	700			mJ
Avalanche Current (Note 1)	I _{AR}	10			A
Repetitive Avalanche Energy (Note 1)	E _{AS}	17			mJ
Operating Temperature Range	T _J	150			°C
Storage Temperature Range	T _{STG}	-55 to +150			°C
Thermal Resistance, Junction to Case	R _{θJC}	0.85	2.6	0.85	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	62.5	62.5	62.5	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	600	-	-	V
Drain-Source Leakage Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	-	-	1	μA
	$V_{DS} = 480\text{ V}, T_c = 125^\circ\text{C}$		-	-	10	
Gate Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	$R_{DS(on)}$	-	0.75	0.9	Ω
Forward Transconductance(Note3)	$V_{DS} = 40\text{ V}, I_D = 5\text{ A}$	g_{fs}	-	9.5	-	S
Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	1609	-	pF
Output Capacitance		C_{oss}	-	136	-	
Reverse Transfer Capacitance		C_{rss}	-	8	-	
Turn-on Delay Time	$I_D = 10\text{ A}, V_{DD} = 300\text{ V}, R_G = 25\Omega(\text{Note3,4})$	$t_d(ON)$	-	26	-	nS
Rise Time		t_r	-	23	-	
Turn-Off Delay Time		$t_d(OFF)$	-	49	-	
Fall Time		t_f	-	27	-	
Total Gate Charge	$I_D = 10\text{ A}, V_{DD} = 480\text{ V}, V_{GS} = 10\text{ V}(\text{Note3,4})$	Q_G	-	32	-	nC
Gate to Source Charge		Q_{GS}	-	8	-	
Gate to Drain Charge		Q_{GD}	-	12	-	

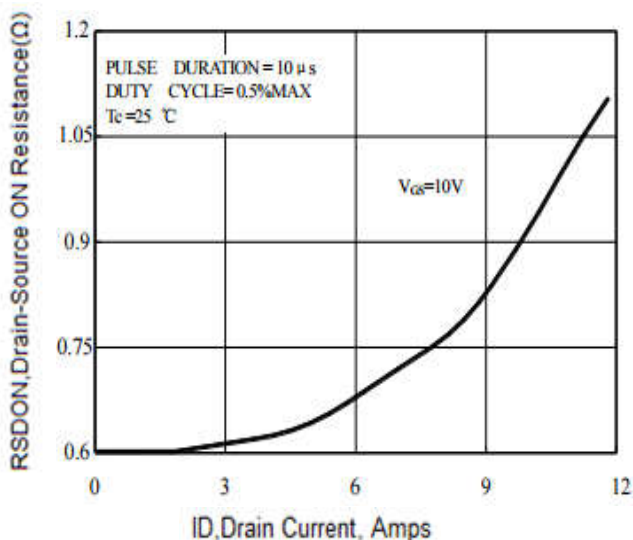
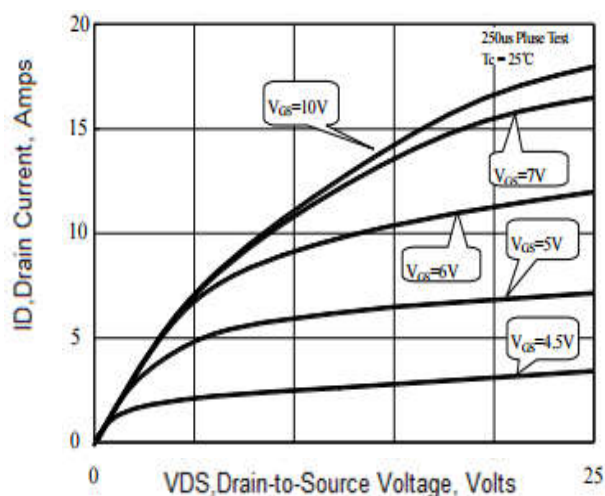
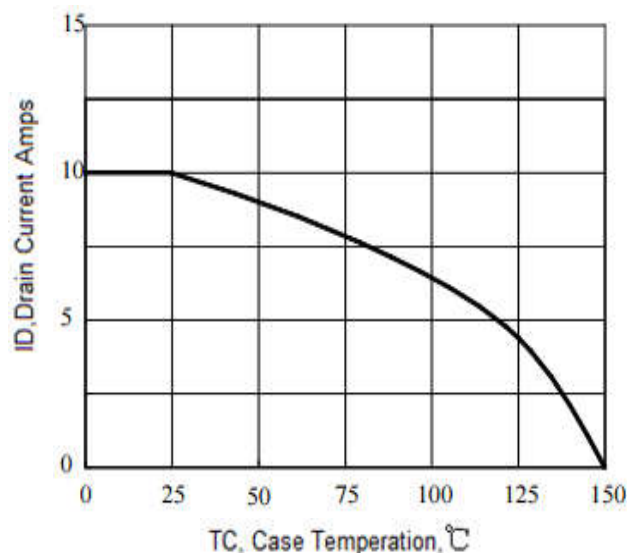
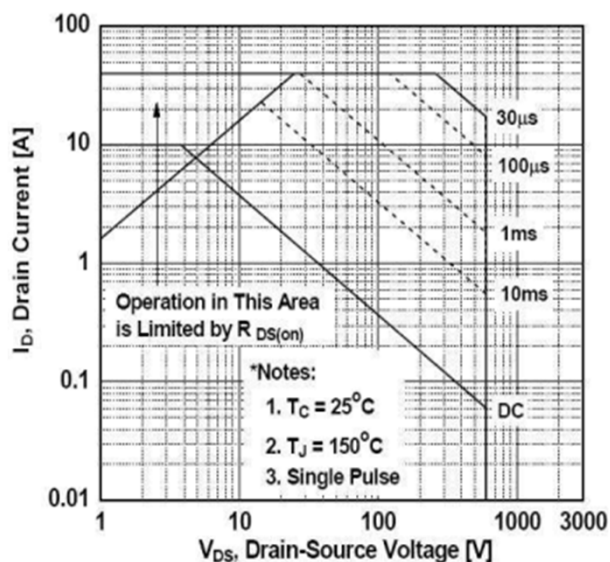
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Maximum Continuous Drain-Source Diode Forward Current		I_S	-	-	10	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}	-	-	40	A
Drain-Source Diode Forward Voltage	$I_{SD} = 10\text{ A}$	V_{SD}	-	-	1.4	V
Reverse Recovery Time	$I_{SD} = 10\text{ A}, V_{GS} = 0\text{ V},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$ (Note3)	t_{rr}	-	500	-	nS
Reverse Recovery Charge		Q_{rr}	-	3	-	uC

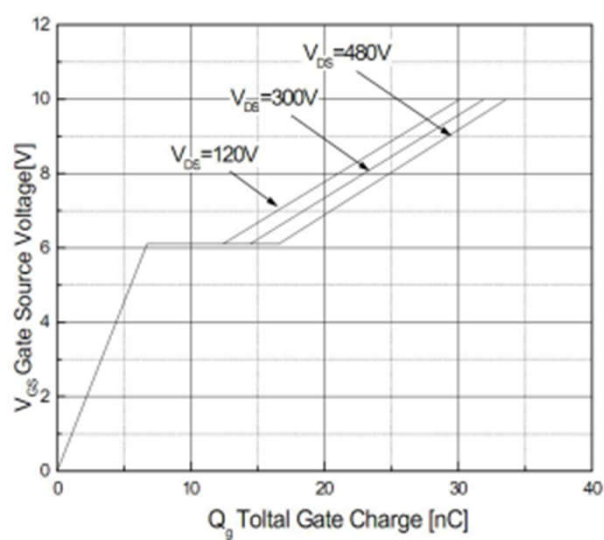
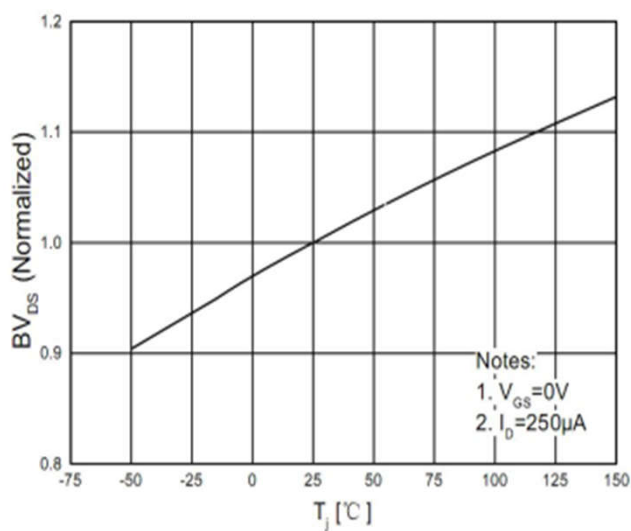
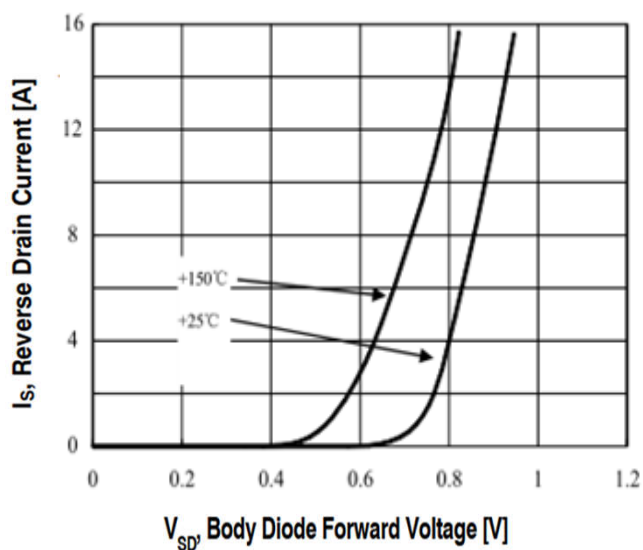
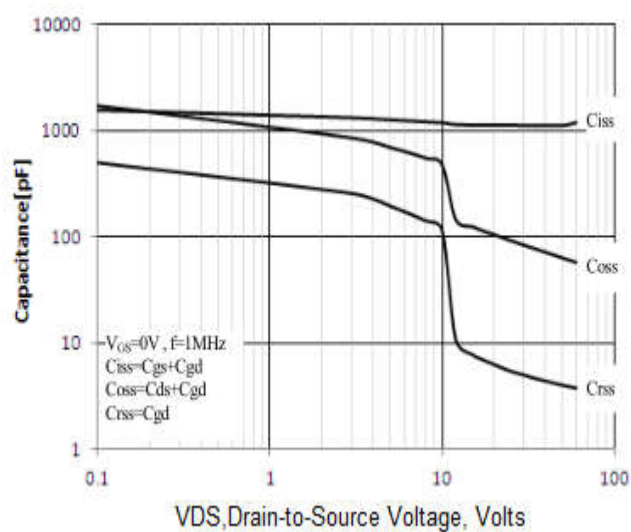
Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $I_{AS} = 10\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 14\text{mH}$, $R_G = 25\Omega$, starting $T_J = 25^\circ\text{C}$.
3. ulse test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycles $\leq 2\%$.
4. Essentially Independent of Operating Temperature.

Ratings and Characteristic Curves



Ratings and Characteristic Curves



Package Outline Dimensions Millimeters

TO-220C

The image shows a technical drawing of a TO-220C package. The front view (left) shows a rectangular body with a circular mounting hole. Dimensions include: A (total width), A2 (hole diameter), F (flange width), E (flange thickness), D (body diameter), S (lead thickness), M (lead length), N (lead pitch), and DIA (lead diameter). The side view (right) shows the package profile with dimensions: C (body height), C1 (flange height), P (lead length), and H (lead diameter).

Dim.	Min.	Max.
A	9.8	10.2
A2	4.8	5.2
C	4.35	4.65
C1	1.45	1.05
D	0.65	0.95
E	3.45	3.75
F	2.85	3.15
G	6.4	6.8
H	0.35	0.65
J	28.68	28.98
K	2.8	3.2
M	1.15	1.45
N	Typical 2.54	
P	2.2	2.6
Q	9	9.4
S	0.15	0.35
U	2.65	2.95
DIA	宽 1.50 ± 0.10	
	深 0.50 MAX	
All Dimensions in millimeter		

TO-220F

The image shows a technical drawing of a TO-220F package. The front view (left) shows a rectangular body with a central circular feature and four mounting holes. Dimensions A, B, C, D, E, F, G, H, and I are indicated. The side view (right) shows the package's profile with dimensions J, K, L, M, N, O, and P. The package has a central circular feature and four mounting holes. The dimensions are as follows:

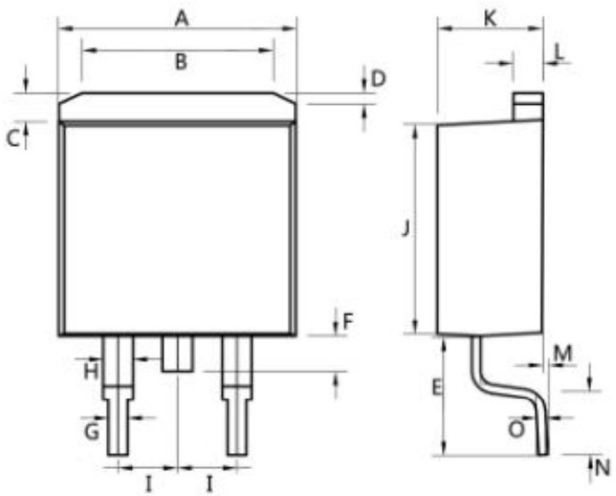
Dim.	Min.	Max.
A	9.95	10.25
B	2.95	3.25
C	1.25	1.45
D	12.95	13.25
E	0.50	0.65
F	3.1	3.3
G	1.30	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.60	4.75
K	2.50	2.65
L	6.35	6.55
M	15.4	16.0
N	2.75	3.05
O	0.48	0.52
P	0.76	0.84

Dim.	Min.	Max.
A	9.95	10.25
B	2.95	3.25
C	1.25	1.45
D	12.95	13.25
E	0.50	0.65
F	3.1	3.3
G	1.30	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.60	4.75
K	2.50	2.65
L	6.35	6.55
M	15.4	16.0
N	2.75	3.05
O	0.48	0.52
P	0.76	0.84

All Dimensions in millimeter

Package Outline Dimensions Millimeters

TO-263

	Dim.	Min.	Max.
	A	10.1	10.2
	B	7.4	7.6
	C	1.3	1.5
	D	0.55	0.75
	E	5.0	6.0
	F	1.4	1.6
	G	0.78	0.86
	H	1.2	1.3
	I	Typ2.54	
	J	8.4	8.6
	K	4.45	4.55
	L	1.25	1.35
	M	0.02	0.1
	N	2.4	2.8
	O	0.36	0.40
All Dimensions in millimeter			